## Origin of High Critical Current Density in MgB<sub>2</sub> Thin Films

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We have fabricated high-quality c-axis-oriented MgB<sub>2</sub> thin films by using a pulsed laser deposition technique. The thin films grown on (1  $\bar{1}$  0 2) Al<sub>2</sub>O<sub>3</sub> substrates show an onset transition temperature of 39.2 K with a sharp transition width of ~ 0.15 K. X-ray diffraction patterns indicate a c-axis-oriented crystal structure perpendicular to the substrate surface. We observed high critical current densities ( $J_c$ ) of ~ 16 MA/cm<sup>2</sup> at 15 K and under self-field, which is comparable to or exceeds those of cuprate high-temperature superconductors. The extrapolation  $J_c$  at 5 K was estimated to be ~ 40 MA/cm<sup>2</sup>, which is the highest record for MgB<sub>2</sub> compounds. At a magnetic field of 5 T, the  $J_c$  of ~ 0.1 MA/cm<sup>2</sup> was detected at 15 K, suggesting that this compound is very promising candidate for the practical applications at high temperature with lower power consumption. As a possible explanation for the high current-carrying capability, the vortex-glass phase will be discussed.

keywords: MgB2, thin film, critical current density